

#### INTRODUCE:

HVGT high voltage silicon rectifier diodes is made of high quality silicon wafer chip and high reliability epoxy resin sealing structure, and through professional testing equipment inspection qualified after to customers.

#### FEATURES:

1. High overload surge capability.
2. High Current,Low Forward Voltage.
3. Avalanche Characteristic.
4. Conform to RoHS and SGS.
5. Epoxy resin molded in vacuumHave anticorrosion in the surface.

#### APPLICATIONS:

1. High voltage power supply rectifier.
2. High voltage rectifier circuit for microwave oven.
3. Other.

#### MECHANICAL DATA:

1. Case: epoxy resin molding.
2. Terminal: welding axis.
3. Net weight: 2.50 grams (approx).

#### SHAPE DISPLAY:



#### Part Marking:

##### Code:

HVM12  
-350  
HVGT

##### Cathode Mark:

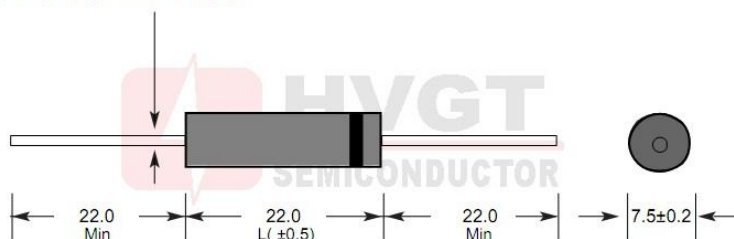


#### SIZE: (Unit:mm)

HVGT NAME: DO-722

#### DO-722 Series

Lead Diameter 1.2mm ±0.02



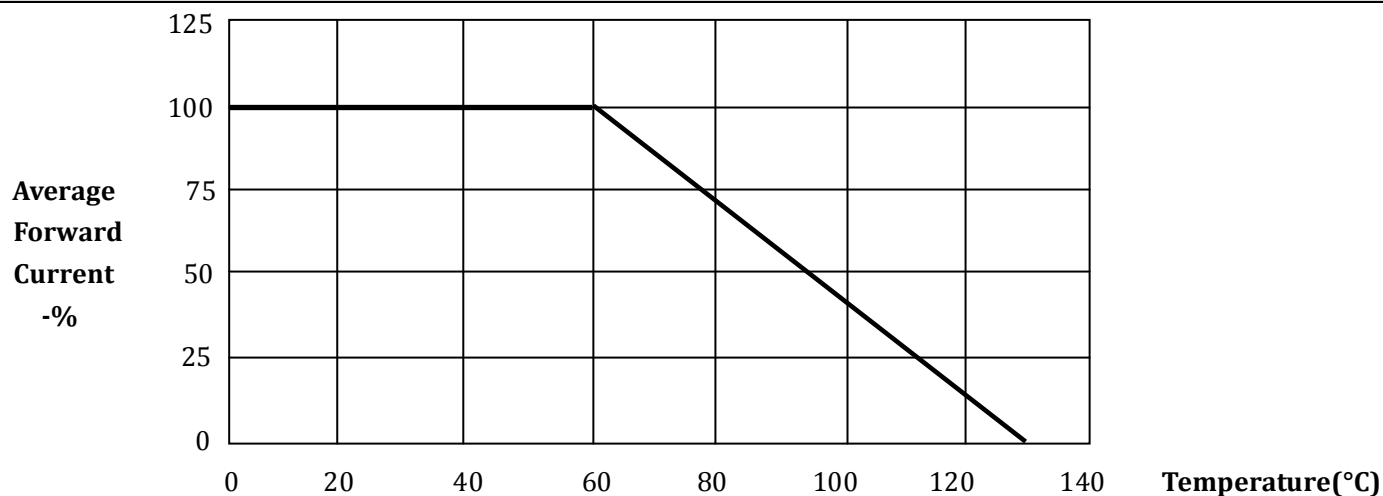
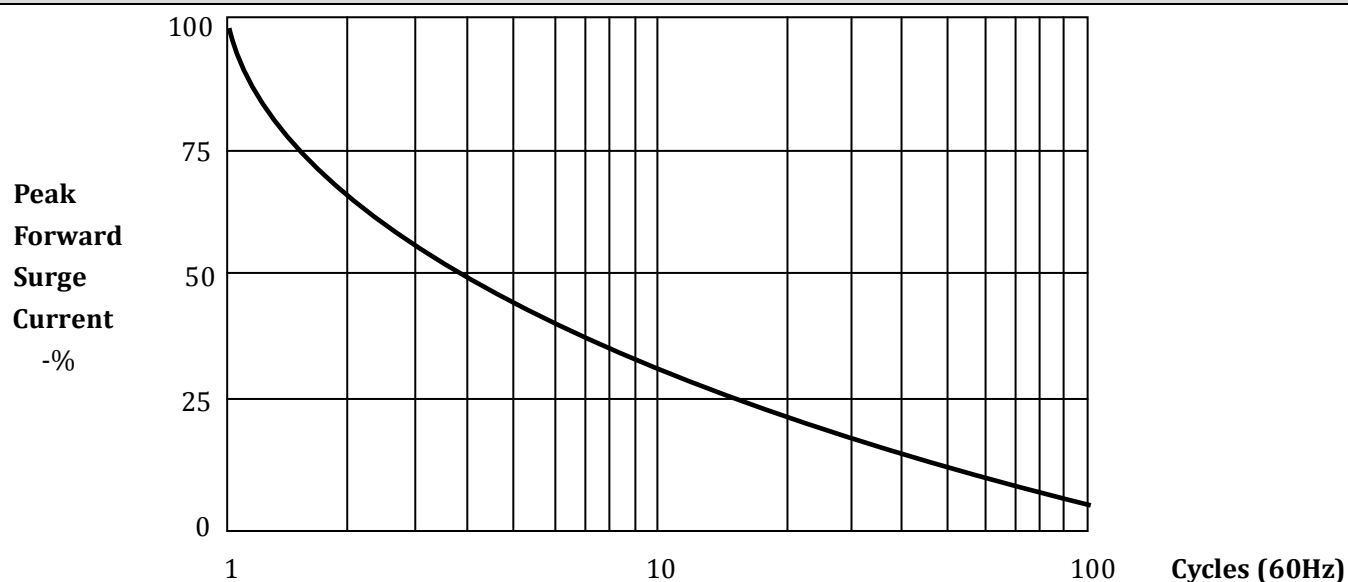
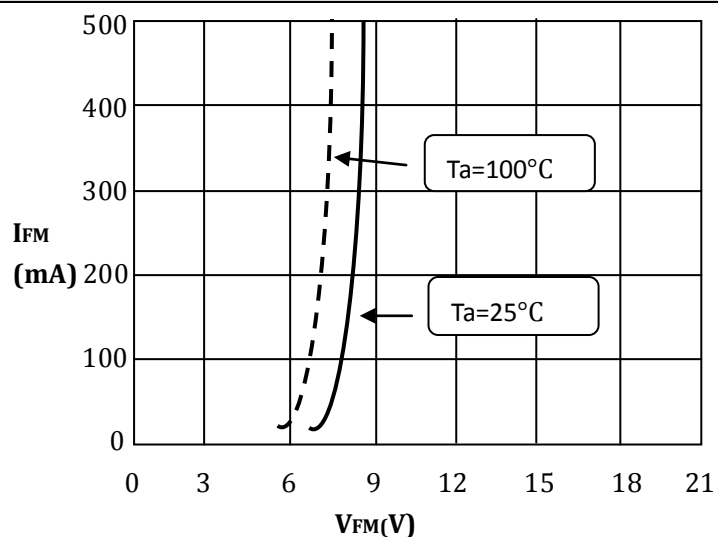
Unit:mm

#### MAXIMUM RATINGS AND CHARACTERISTICS: Ta=25°C (Absolute Maximum Ratings)

| Items                                | Symbols    | Condition                                                       | Data Value | Units            |
|--------------------------------------|------------|-----------------------------------------------------------------|------------|------------------|
| Repetitive Peak Reverse Voltage      | $V_{RRM}$  |                                                                 | 12         | kV               |
| Average Forward Current Maximum      | $I_{FAVM}$ | 60Hz Half-Sine Wave, Resistance Load,<br>$T_a=60^\circ\text{C}$ | 350        | mA               |
| Non-Repetitive Forward Surge Current | $I_{FSM}$  | 60Hz Half-Sine Wave; 8.3ms; 1Cycle                              | 30         | A                |
| Reverse surge current                | $I_{RSM}$  | $W_p=1\text{ms}$ , Rectangular-Wave, One-shot,                  | 100        | mA               |
| Junction Temperature                 | $T_j$      |                                                                 | 130        | $^\circ\text{C}$ |
| Allowable Operation Case Temperature | $T_c$      |                                                                 | -40~+130   | $^\circ\text{C}$ |
| Storage Temperature                  | $T_{STG}$  |                                                                 | -40~+130   | $^\circ\text{C}$ |

#### ELECTRICAL CHARACTERISTICS: Ta=25°C (Unless Otherwise Specified)

| Items                         | Symbols  | Condition                                                                | Data value | Units         |
|-------------------------------|----------|--------------------------------------------------------------------------|------------|---------------|
| Maximum Forward Voltage Drop  | $V_{FM}$ | at $25^\circ\text{C}$ ; at $I_{FAVM}$                                    | 10         | V             |
| Maximum Reverse Current       | $I_{R1}$ | at $25^\circ\text{C}$ ; at $V_{RRM}$                                     | 5.0        | $\mu\text{A}$ |
|                               | $I_{R2}$ | at $100^\circ\text{C}$ ; at $V_{RRM}$                                    | 50         | $\mu\text{A}$ |
| Maximum Reverse Recovery Time | $T_{RR}$ | at $25^\circ\text{C}$ ; $I_F=0.5I_R$ ; $I_R=I_{FAVM}$ ; $I_{RR}=0.25I_R$ | --         | nS            |
| Reverse Breakdown Voltage     | $V_Z$    | at $25^\circ\text{C}$ ; $I_R=100\mu\text{A}$                             | 12.5       | kV            |

**Forward Current Derating Curves**

**Non-Repetitive Surge Current**

**Forward Characteristics**

**Reverse Characteristics**
